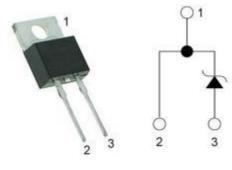


Product Summary

 $V_R = 650 V$ $I_F = 20A (T_C=148^{\circ}C)$ $Q_C = 44nC (V_R=400V)$



TO-220-2

Features

- Zero Forward/Reverse Recovery Current
- High Blocking Voltage
- High Frequency Operation
- Positive Temperature Coefficient on V_F
- Temperature Independent Switching Behavior

Applications

Motor Drives

Solar Inverters

Benefits

- Higher System Efficiency
- Parallel Device Convenience without thermal runaway
- Higher Temperature Application
- No Switching loss
- Hard Switching & Higher Reliability
- Environmental Protection
- AC/DC converters
- DC/DC converters
- Uninterruptable power supplies

Maximum Rating	S (T _c =25°C unless otherwise	specified)
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Parameter	Symbol	Test conditions	Value	Unit
Peak Repetitive Reverse Voltage	VRRM		650	V
Peak Reverse Surge Voltage	V _{RSM}		650	V
DC Blocking Voltage	VR		650	V
Continuous Forward Current	ŀF	Tc=25°C Tc=135°C Tc=148°C	58 25 20	A
Non repetitive Forward Surge Current	IFSM	$T_c = 25^{\circ}C$, $t_p=10$ ms, Half Sine Pulse $T_c = 110^{\circ}C$, $t_p=10$ ms, Half Sine Pulse	120 110	A
Repetitive peak Forward Surge Current	IFRM	$T_c = 25^{\circ}C, t_p=10 \text{ ms},$ Freq = 0.1Hz, 100 cycles, Half Sine Pulse $T_c = 110^{\circ}C, t_p=10 \text{ ms},$ Freq = 0.1Hz, 100 cycles, Half Sine Pulse	110 100	A
Total power dissipation	PD	Tc=25°C	176	W
Operating Junction Temperature	TJ		-55 to 175	°C
Storage Temperature	T _{STG}		-55 to 175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



Electrical Characteristics

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
DC Blocking Voltage	V _{DC}	l _R = 250µA,TJ = 25°C	650			V
		l⊧ = 20A, T」 = 25°C		1.5	1.8	V
Forward Voltage	VF	l⊧ = 20A, T」 = 125°C		1.6	.5 1.8 .6 .7 20 80 20 50 14 .7	V
-		l⊧ = 20A, T」 = 175°C		1.7		V
		V _R = 650V, T _J = 25°C		20	80	uA
Reverse Current	R	V _R = 650V, T _J = 125°C		120		uA
		V _R = 650V, T _J = 175°C		250		uA
Total Capacitive Charge	Qc	V_{R} = 400V, T_{J} = 25°C		44		nC
Total Capacitance		V_R = 1V, T _J = 25°C, Freq = 1MHz		770		
	С	V_R = 200V, T _J = 25°C, Freq = 1MHz		90		pF
		V _R = 400V, T _J = 25°C, Freq = 1MHz		64		

Note: This is a majority carrier diode, so there is no reverse recovery charge

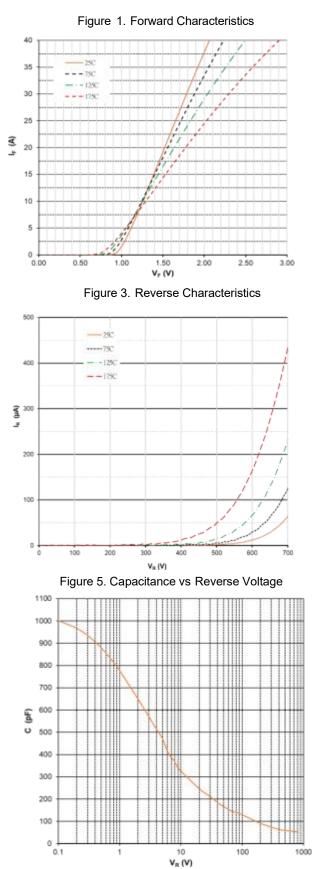
Thermal Characteristics

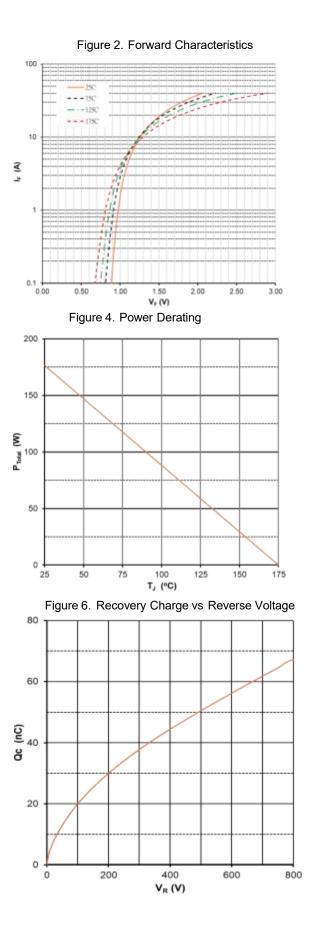
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Thermal Resistance	R _{th(j-c)}	junction-case		0.85		°C/W

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Typical Electrical Curves





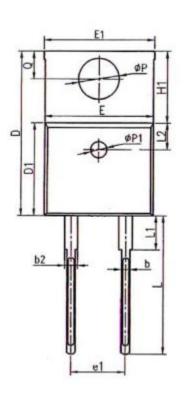
Revision 2.0

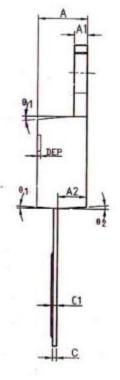


CC3D20065A Silicon Carbide Schottky Diode

Package Dimensions

(TO-220-2 Package)





SYMBOL		MM		INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185
A1	1.22	1.27	1.32	0.048	0.050	0.052
A2	2.59	2.69	2.79	0.102	0.106	0.110
b	0.77	0.813	0.90	0.030	0.032	0.035
b2	1.20	1.27	1.36	0.047	0.050	0.054
0	0.34	0.381	0.47	0.013	0.015	0.019
c1	0.40	0.559	0.60	0.016	0.022	0.024
D	14.70	15.00	15.30	0.579	0.591	0.602
D1	8.60	8.70	8.80	0.339	0.343	0.346
E	10.06	10.16	10.26	0.396	0.400	0.404
E1	10.10	10.25	10.35	0.398	0.404	0.407
E2	10.00	10.10	10.20	0.394	0.398	8.402
	2.54 BSC			2	0.100	BSC
e1		5.08 BSC			0.200	BSC
H1	6.10	6.30	6.50	0.240	0.248	0.256
L	13.20	13.40	13.50	0.520	9.528	0.531
L1	+	3.75	4.00	. /	0.148	0.157
L2		2.50	REF		0.098	REF
ΦP	3.76	3.84	3.88	0.148	0.151	0.153
Q	2.60	2,743	2.90	0.102	0.108	0.114
81	5*	7*	9*	5*	7*	9*
82	1.	3*	5*	1*	3*	5*
ΦP1	1.40	1,50	1.60	0.055	0.059	0.063
DEP	0.05	0.10	0.20	0.002	0.004	0.008

Part Number	Package	Packing	Marking	M.O.Q
CC3D20065A	TO-220-2	50pcs / Tube	CC3D20065A	500



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